

FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)	ATTY. DOCKET NO. MICRON.098DV1	APPLICATION NO. Unknown
	APPLICANT Basceri et al.	
	FILING DATE Herewith	GROUP Unknown

Jc079 U.S. PTO
 09/971955
 10/04/01

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
CN		5,335,138	08/02/94	Sandhu et al.			
CN		5,506,166	04/09/96	Sandhu et al.			
CN		5,717,234	02/10/98	Si et al.			
CN		5,783,253	07/21/98	Roh			
CN		6,010,931	01/04/00	Sun et al.			
CN		6,117,482	09/12/00	Kawahara et al.			
CN		6,136,639	10/24/00	Seon			

FOREIGN PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
							YES NO

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
CN	Hiromi Itoh et al., "Integration of BST Thin Film for Dram Fabrication", Integrated Ferroelectrics, 1995, Vol. 11, pp. 101-109
CN	C. Basceri, "An Important Failure Mechanism in MOCVD (Ba,Sr) TiO Thin Films: Resistance Degradation", Ferroelectric Thin Films IV, Materials Research Society, 1998, pp. 9-14

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 091701

EXAMINER	2964	DATE CONSIDERED	2-20-03
*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.			